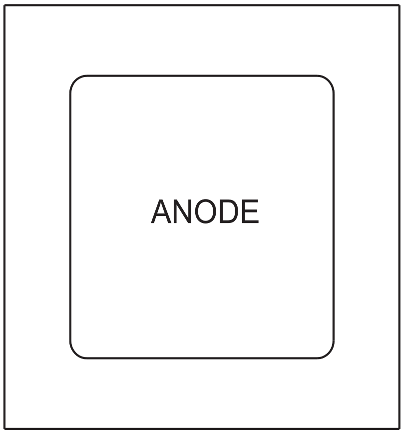
Central™
Semiconductor Corp.

PROCESS CPZ18
Zener Diode
0.5 Watt Zener Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 X 14 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	7.5 X 7.5 MILS
Top Side Metalization	Al - 13,000Å TYP
Back Side Metalization	Au - 14,000Å TYP

Geometry



R0

GROSS DIE PER 4 INCH WAFER
61,141

PRINCIPAL DEVICE TYPES
CMPZ5221B
THRU
CMPZ5234B

145 Adams Avenue
Hauppauge, NY 11788 USA
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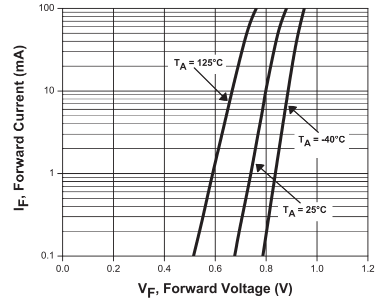
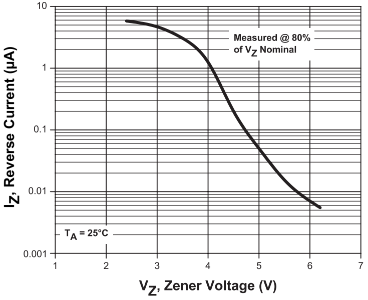
Typical Electrical Characteristics

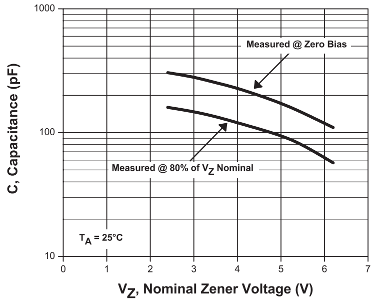
Forward Voltage



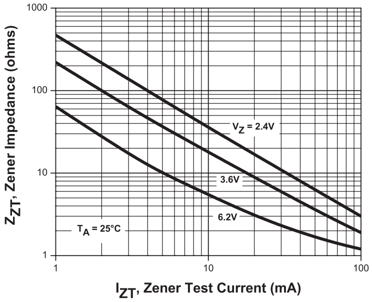
Reverse Leakage Characteristics



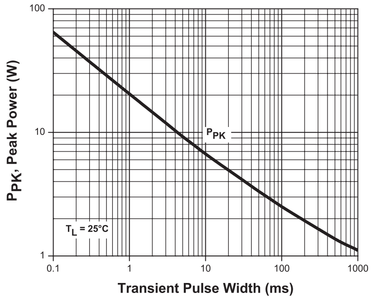
Capacitance



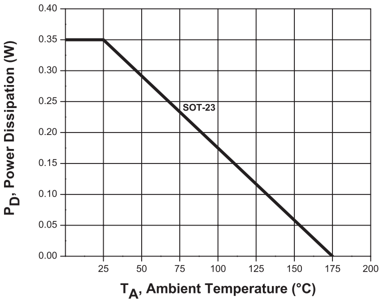
Zener Impedance



Transient Peak Power Capacity



Power Derating



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